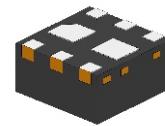


# CMSA06CP02A06K-HF

P-Channel  
RoHS Device  
Halogen Free



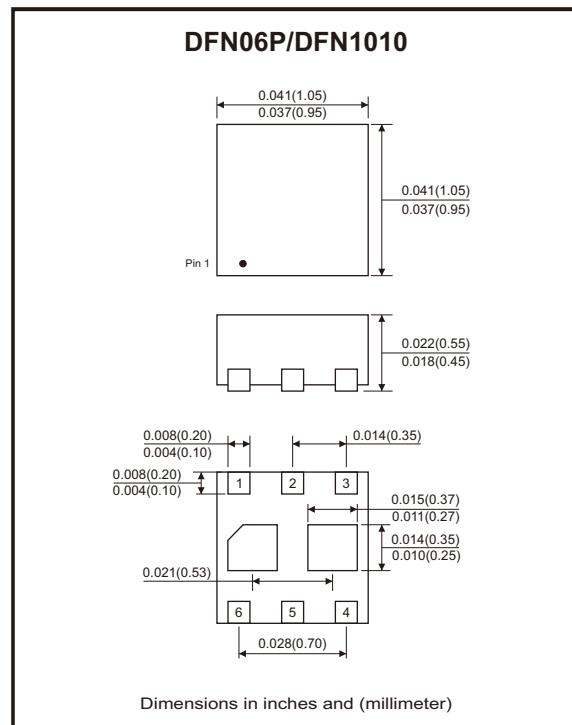
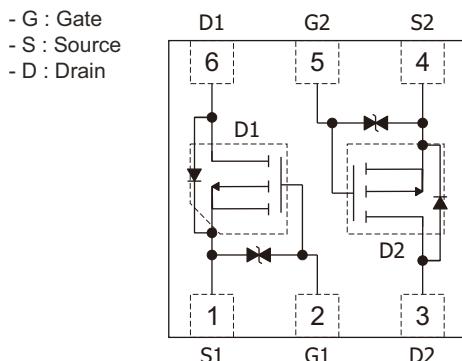
## Features

- Surface mount package.
- Reliable and rugged.
- ESD protection.
- Human body model (HBM) 2kV
- Charge device model (CDM) 1kV

## Mechanical data

- Case: DFN06P/DFN1010 package, molded plastic.
- Mounting position: Any.

## Circuit Diagram



## Maximum Ratings (at $T_A=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-source voltage	$V_{DS}$	-20	V
Gate-source voltage	$V_{GS}$	$\pm 8$	V
Continuous drain current	$I_D$	-900	mA
Power dissipation	$P_D$	600	mW
Thermal resistance, junction to ambient @ $T_A=25^\circ\text{C}$	$R_{\theta JA}$	164	$^\circ\text{C}/\text{W}$
Operating junction and storage temperature range	$T_J, T_{STG}$	-55 to +150	$^\circ\text{C}$

**Electrical Characteristics** (at  $T_A=25^\circ\text{C}$  unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
<b>Static Electrical Characteristics</b>						
Drain-source breakdown voltage	$\text{BV}_{\text{DSS}}$	$V_{\text{GS}} = 0\text{V}, I_{\text{D}} = -250\mu\text{A}$	-20			V
Zero gate voltage drain current	$I_{\text{DSS}}$	$V_{\text{DS}} = -16\text{V}, V_{\text{GS}} = 0\text{V}$			-0.6	$\mu\text{A}$
Gate leakage current	$I_{\text{GSS}}$	$V_{\text{GS}} = \pm 8\text{V}, V_{\text{DS}} = 0\text{V}$			$\pm 10$	$\mu\text{A}$
Gate threshold voltage	$V_{\text{GS(th)}}$	$V_{\text{DS}} = V_{\text{GS}}, I_{\text{D}} = -250\mu\text{A}$	-0.3		-1.0	V
Drain source on-state resistance	$R_{\text{DS(on)}}$	$V_{\text{GS}} = -4.5\text{V}, I_{\text{D}} = -500\text{mA}$		450	560	$\text{m}\Omega$
		$V_{\text{GS}} = -2.5\text{V}, I_{\text{D}} = -500\text{mA}$		570	780	
		$V_{\text{GS}} = -1.8\text{V}, I_{\text{D}} = -100\text{mA}$		690	1100	
		$V_{\text{GS}} = -1.5\text{V}, I_{\text{D}} = -50\text{mA}$		820	1400	
		$V_{\text{GS}} = -1.2\text{V}, I_{\text{D}} = -10\text{mA}$		1160	2200	
Drain forward voltage	$V_{\text{SD}}$	$V_{\text{GS}} = 0\text{V}, I_{\text{S}} = -300\text{mA}$	-0.4		-1.2	V
<b>Dynamic Characteristics</b>						
Input capacitance	$C_{\text{iss}}$	$V_{\text{DS}} = -10\text{V}, V_{\text{GS}} = 0\text{V}, f = 1\text{MHz}$		40		$\text{pF}$
Output capacitance	$C_{\text{oss}}$			12		
Reverse transfer capacitance	$C_{\text{rss}}$			6		

## Typical Rating and Characteristic Curves (CMSA06CP02A06K-HF)

Fig.1 - On-Region Characteristics

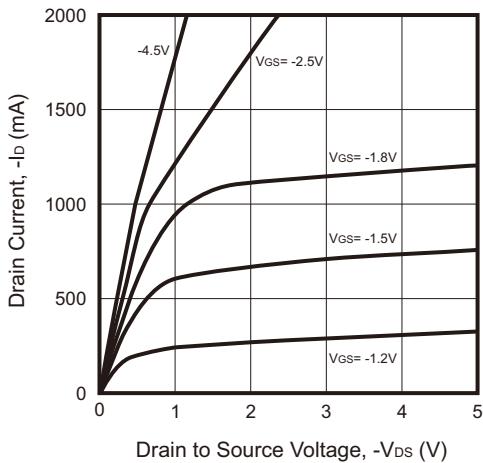


Fig.2 - Transfer Characteristics

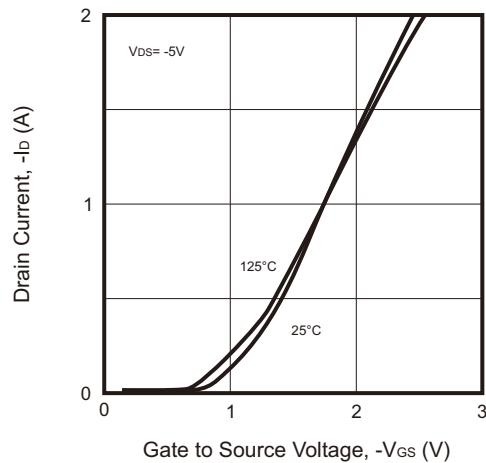


Fig.3 - On-Resistance vs. Drain Current Gate Voltage

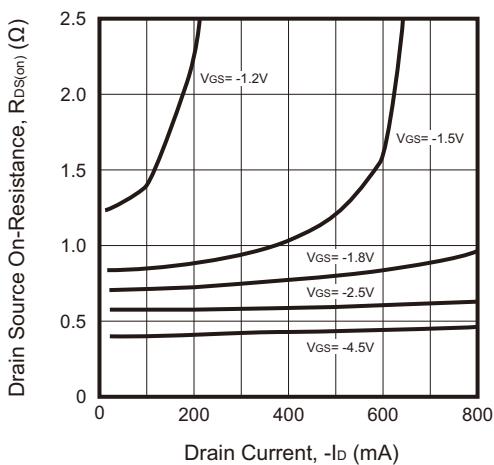


Fig.4 - On-Resistance Variation with Temperature

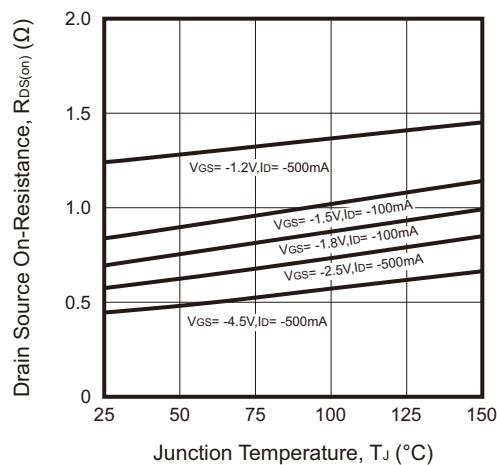


Fig.5 - On-Resistance vs. Gate to Source Voltage

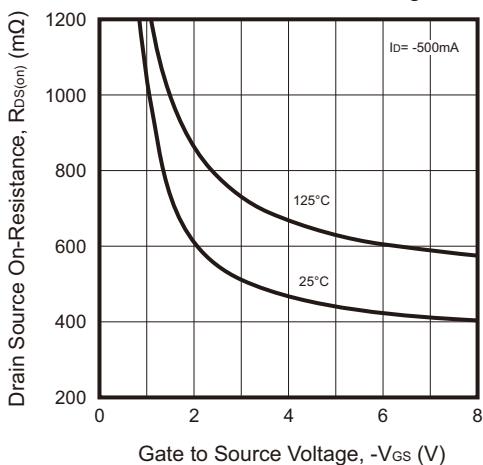
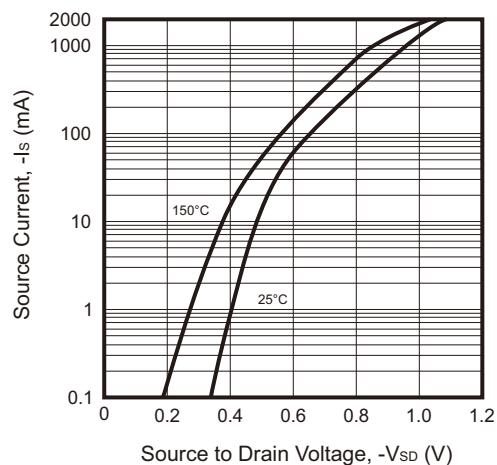


Fig.6 - Diode Forward Voltage vs. Current



## Typical Rating and Characteristic Curves (CMSA06CP02A06K-HF)

Fig.7 - Gate Threshold Variation  
vs. Ambient Temperature

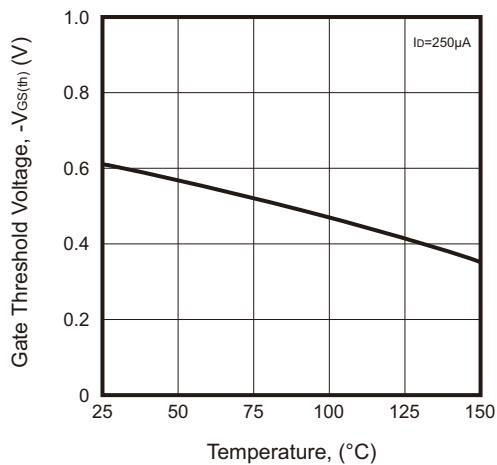


Fig.8 - Breakdown Voltage vs. Temperature

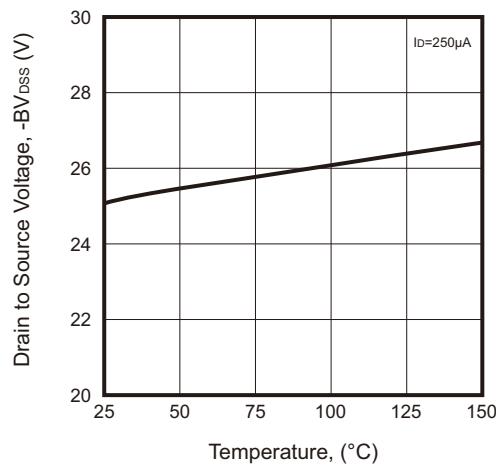
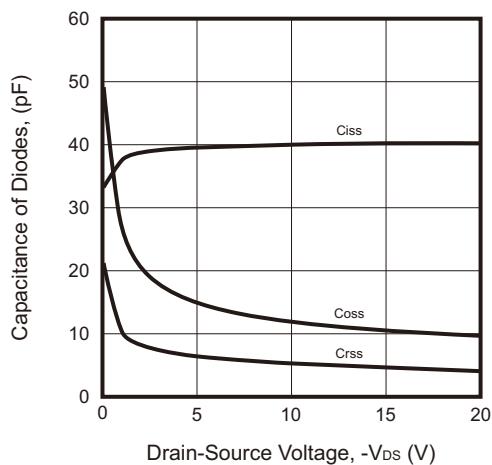
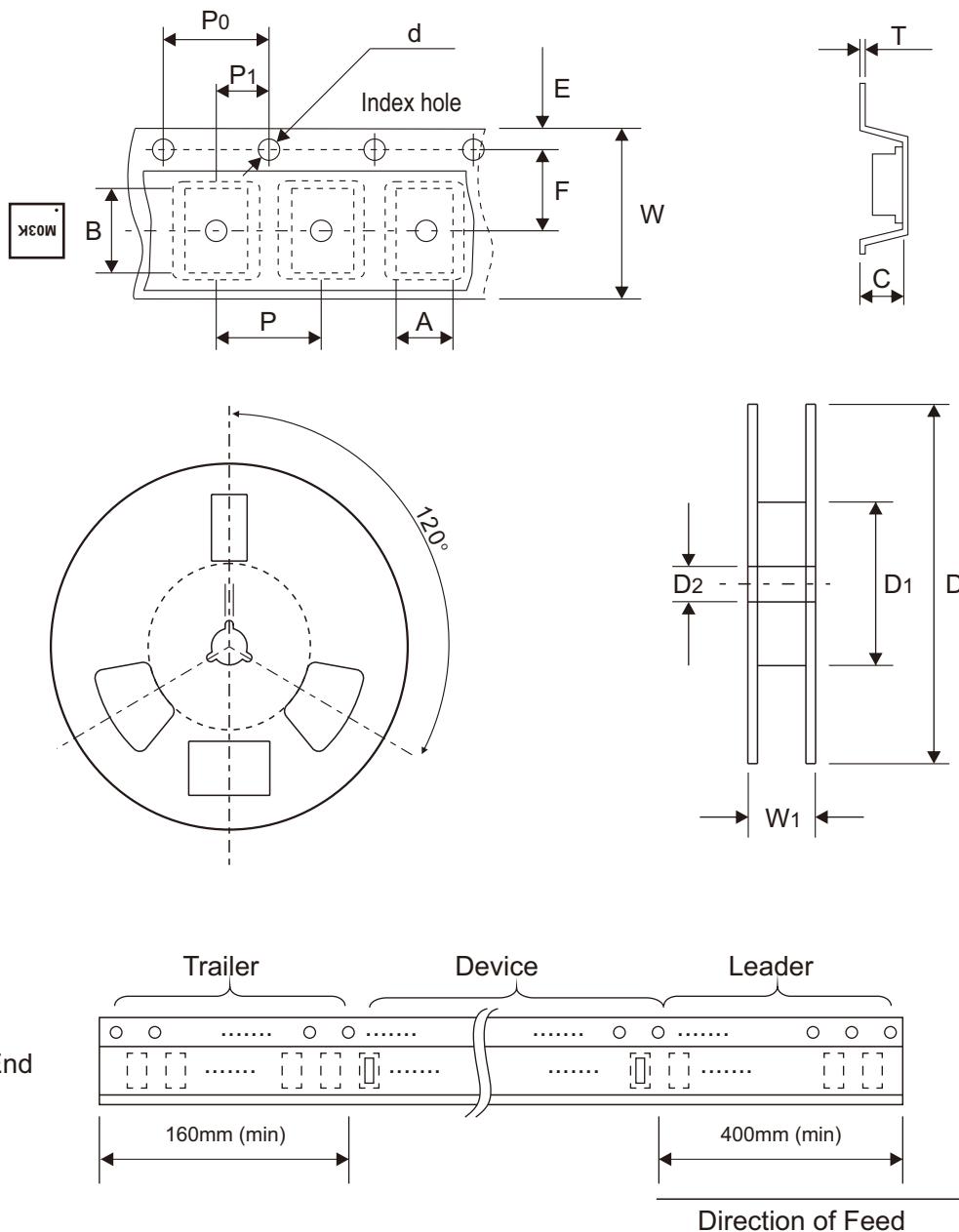


Fig.9 - Capacitance of Diodes



## Reel Taping Specification



	SYMBOL	A	B	C	d	D	D1	D2
DFN06P/ DFN1010	(mm)	$1.13 \pm 0.05$	$1.13 \pm 0.05$	$0.65 \pm 0.05$	$1.50 + 0.10$ $- 0.00$	$178.00 \pm 1.00$	$60.00 \pm 0.50$	$13.50 \pm 0.20$
	(inch)	$0.044 \pm 0.002$	$0.044 \pm 0.002$	$0.026 \pm 0.002$	$0.059 + 0.004$ $- 0.000$	$7.008 \pm 0.039$	$2.362 \pm 0.020$	$0.531 \pm 0.008$

	SYMBOL	E	F	P	P0	P1	T	W	W1
DFN06P/ DFN1010	(mm)	$1.75 \pm 0.10$	$3.50 \pm 0.05$	$4.00 \pm 0.10$	$4.00 \pm 0.10$	$2.00 \pm 0.05$	$0.20 \pm 0.05$	$8.00 + 0.30$ $- 0.10$	$12.00 + 0.50$ $- 0.00$
	(inch)	$0.069 \pm 0.004$	$0.138 \pm 0.002$	$0.157 \pm 0.004$	$0.157 \pm 0.004$	$0.079 \pm 0.002$	$0.008 \pm 0.002$	$0.315 + 0.012$ $- 0.001$	$0.472 + 0.020$ $- 0.000$

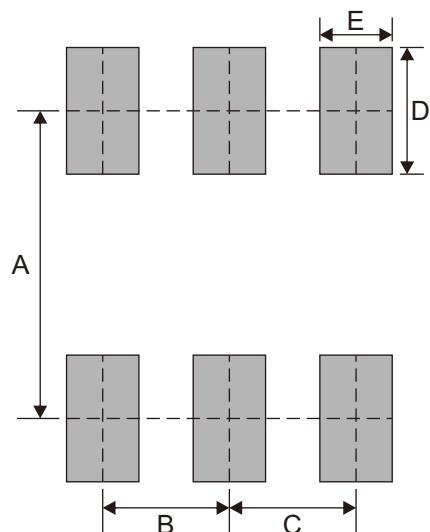
## Marking Code

Part Number	Marking Code
CMSA06CP02A06K-HF	.M06K



## Suggested P.C.B. PAD Layout

SIZE	DFN06P /DFN1010	
	(mm)	(inch)
A	0.85	0.033
B	0.35	0.014
C	0.35	0.014
D	0.35	0.014
E	0.20	0.008



## Standard Packaging

Case Type	REEL PACK	
	REEL ( pcs )	Reel Size (inch)
DFN06P /DFN1010	5,000	7